32 位高温闪存存储器
此存储器具有串行外设接口 (SPI) 接口

查询样品: SM28VLT32-HT

特性

- 针对高温环境的 **32** 兆位闪存
- 串行外设接口 **(SPI)** 兼容（模式 **0** 和 **3**）
- 用于 **IO** 的 **3.3V** 电源，用于内核的 **1.9V** 电源
- **2M x 16** 位字存取
- 异步读取、写入和擦除操作
- 只在 **-55°C** 至 **125°C** 温度范围内支持擦除操作
- **12MHz** 最高时钟频率
- 使用寿命：**1000** 个程序和擦除周期
- 数据保留：**1000** 小时
- **ESD** 保护：**2kV HBM**，**500V CDM**
- **8mm x 20mm 14** 引脚陶瓷 **HKN** 封装和 **KGD**（裸芯片）封装

应用范围

- 浅孔能源钻井
- 测试和测量仪器
- 极端环境下的地震数据采集
- 在极高和极低温度环境下的通用数据采集应用

支持极端温度环境下的应用

- 受控基线
- 一个组装和测试场所
- 一个制造场所
- 极端（**-55°C** 至 **210°C**）温度范围内可用 (1)
- 延长的产品生命周期
- 延长的产品变更通知
- 产品可追溯性
- 德州仪器 （**TI**） 高温产品利用高度优化的硅（芯片）解决方案，此解决方案对设计和制造工艺进行了提升以在拓展的温度范围内大大地提高性能。 在最大额定温度下，所有器件可连续正常运行**1000** 小时。

HKN 封装
(顶视图**)**

(1) 可定制工作温度范围

说明

SM28VLT32 是一款 32 兆位闪存存储器，此存储器设计用于存储程序代码和/或采集到的数据。 这个器件的宽温度额定值使得它非常适合于需要在恶劣环境中可靠执行的应用。 SM28VLT32 借助于它的串行外设接口 (SPI) 提供低引脚数量以实现额外的可靠性以及这些应用中的简便组装。

存储器被分区成扇区以提供每个 16 位的 2M 字寻址。 因此，存储器地址为 21 位宽。

SM28VLT32 支持串行外设接口以在闪存存储器中读取/写入/擦除数据。 此接口与模式 0 (CPOL = 0，CPHA = 0) 和 3 (CPOL = 1，CPHA = 1) 兼容。 将 CS# 置为有效将使器件进入通信模式。 在 CS# 被取消置位时，器件忽略 SPI 引脚上的所有活动。 如图 1中所示，为了在应用中实现较大存储器，可通过独立控制 CS# 引脚由一个单个主控器件来控制多个 SM28VLT32 器件。 将 HOLD# 引脚置为有效（同时 CS# 也被置位）将使器件忽略其它 SPI 输入引脚（SCK 和 SI）上的活动。

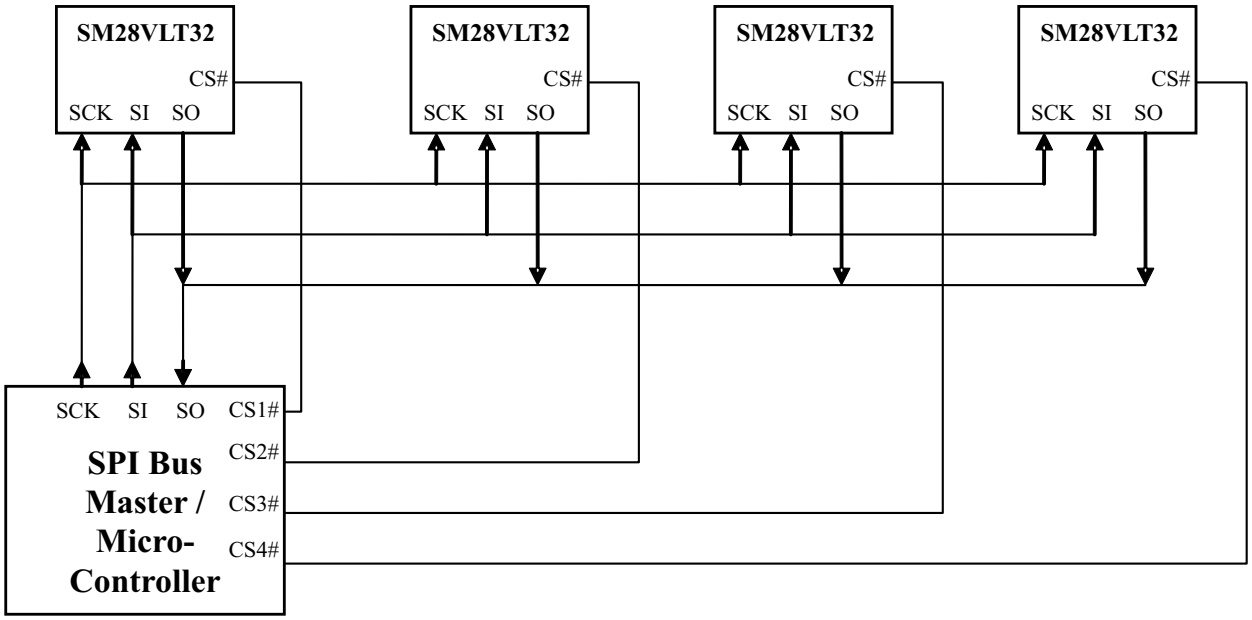


图 **1.** 显示使用多个 **SM28VLT32** 器件来实现较大存储器的系统方框图

SM28VLT32 使用 WP# 引脚来支持一个硬件数据保护机制。 如果 WP# 为低电平，擦除和编程操作被禁止。

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ORDERING INFORMATION(1)

T_J	PACKAGE	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–55°C to 210°C	14-Pin HKN	SM28VLT32SHKN	28VLT32SHKN
	KGD (Bare Die)	SM28LVT32SKGD3	N/A

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

		UNIT
VIO	Supply voltage range (for IO)	–0.3 V to 4.5 V
VCORE	Supply voltage range (for Core)	–0.3 V to 2.5 V
V_I	Input voltage range	–0.2 V to (V_{IO} + 0.2)
V_O	Output voltage range	–0.2 V to (V_{IO} + 0.2)
ESD	Electrostatic discharge (HBM, 1.5 kΩ, 100 pF)	> 2000 V
T_J	Operating junction temperature range	–55°C to 215°C

(1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

PACKAGE DISSIPATION RATINGS

PACKAGE	θ_{JA} THERMAL IMPEDANCE JUNCTION TO AMBIENT	θ_{JC} THERMAL IMPEDANCE JUNCTION TO CASE (THERMAL PAD)	θ_{JB} THERMAL IMPEDANCE JUNCTION TO BOARD
HKN	63°C/W	0.84°C/W	55°C/W

RECOMMENDED OPERATING CONDITIONS

		MIN	TYP	MAX	UNIT
VIO	Device supply voltage for IO	3.1	3.3	3.6	V
VCORE	Device supply voltage for Core	1.8	1.9	1.98	V
T_J	Junction temperature	–55		210	°C

ELECTRICAL CHARACTERISTICS: IO

V_{IO} = 3.1 V to 3.6 V, V_{Core} = 1.8 V to 1.98 V, T_J = –55°C to 210°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{IH}	Input high voltage		2.5			V
V_{IL}	Input low voltage				0.9	V
I_{OH}	Output high current	$V_{OH} = V_{OHmin}$	-8			mA
I_{OL}	Output low current	$V_{OL} = V_{OLmax}$			8	mA
V_{OH}	Output high voltage	$I_{OH} = I_{OHmin}$	2.8			V
V_{OL}	Output low voltage	$I_{OL} = I_{OLmax}$			0.8	V
C_I	Input capacitance			6.5		pF

ELECTRICAL CHARACTERISTICS: MEMORY

V_{IO} = 3.1 V to 3.6 V, V_{Core} = 1.8 V to 1.98 V, T_J = –55°C to 210°C (unless otherwise noted)

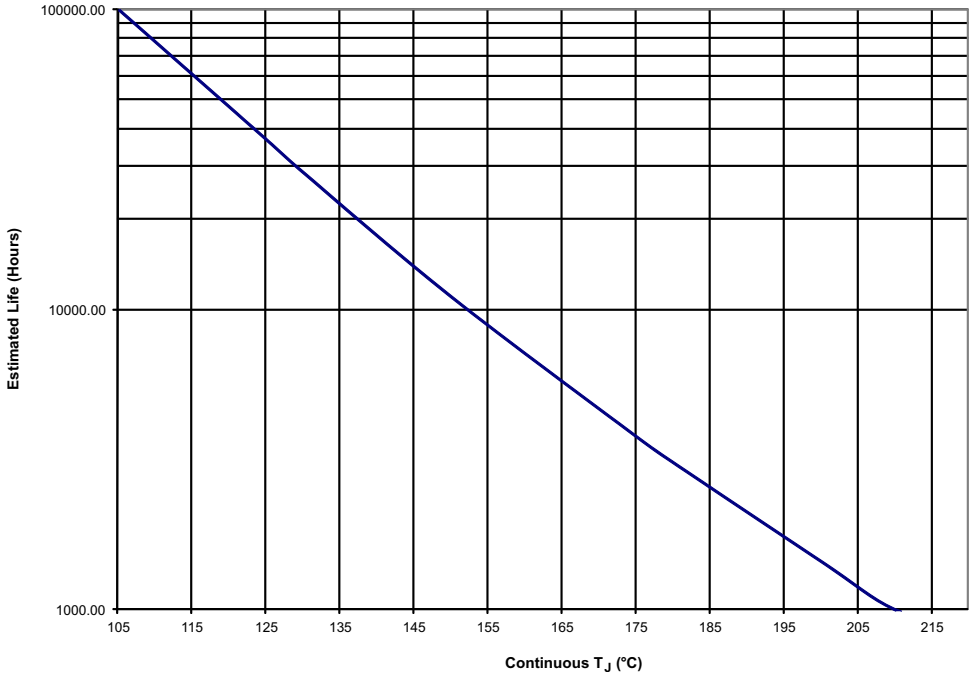
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{Life}	Continuous operating life		1000			hrs
$I_{DDVCORE}$				127	160	mA
I_{DDVIO}				14	22	mA
	Erase current	-55°C to 125°C		76		mA
	Program current			85		mA
	Sector erase time	-55°C to 125°C		2	3	s
	Program time 1 16-bit word			30	300	µs
N_f	Flash endurance for the array (write/erase cycles)	T_J = 30°C		1000		cycles

ELECTRICAL CHARACTERISTICS: SPI(1)(2)

V_{IO} = 3.1 V to 3.6 V, V_{Core} = 1.8 V to 1.98 V, T_J = –55°C to 210°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_{SCK}	SPI input clock frequency(3)				10	MHz
f_{CLK}	Flash clock(3)				12	MHz
t_{WH}	Clock high time		25			ns
t_{WL}	Clock low time		25			ns
t_{SU1}	CS# setup time before SCK		15			ns
t_{SU2}	SI setup time before SCK		10			ns
t_{OEN}	CS# to SO enabled	CL = 16 pF	5		16.5	ns
t_{DIS}	CS# to SO disabled(4)	CL = 16 pF	5		16.5	ns
t_{HD}	Data hold time after SCK		5			ns
t_r/t_f		10% to 90% on all input pins			20	ns
t_V	Clock low to data valid	CL = 50 pF		15	30	ns

(1) See Figure 3.
(2) AC parameters apply to t_r/t_f of 5 ns.
(3) The ratio of f_{CLK}/f_{SCK} must be 6/5 or higher to insure proper asynchronous operation. Operation below 12 MHz is acceptable, however, some configuration changes are required to set proper internal timing. See Provisions for Operating With f_{CLK} Frequencies Less than 12 MHz for details if planned f_{CLK} usage is below 12 MHz.
(4) Disable parameters are specified when the outputs are no longer driven.



(1) See datasheet for absolute maximum and minimum recommended operating conditions.

(2) Silicon operating life design goal is 10 years at 105°C junction temperature (does not include package interconnect life).

(3) The predicted operating lifetime vs. junction temperature is based on reliability modeling and available qualification data.

Figure 2. SM28VLT32-HT Operating Life Derating Chart

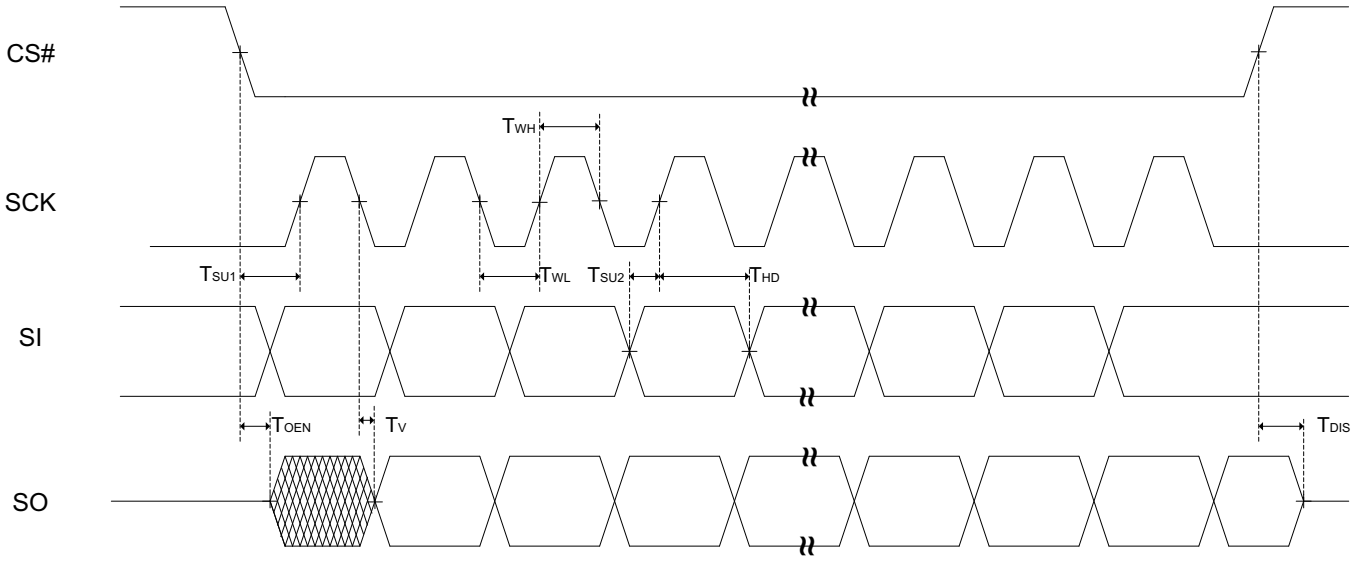
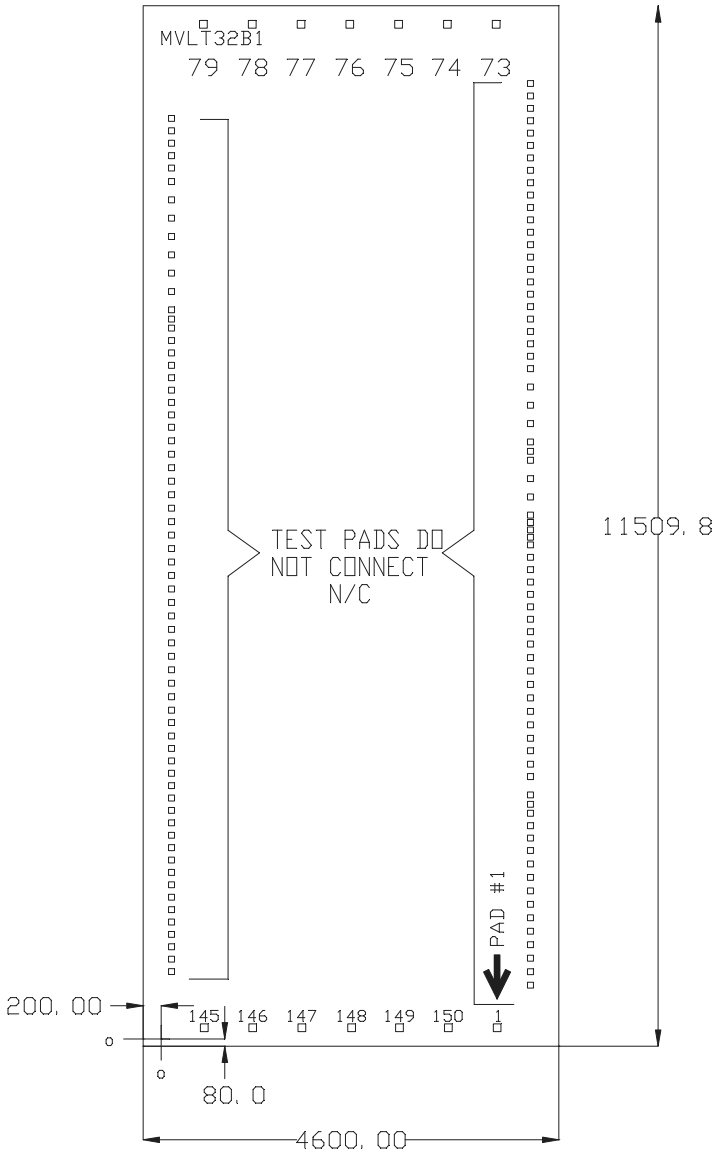


Figure 3. SPI Timing Diagram

DIE LAYOUT



A. All dimensions are in microns

B. Substrate can either float or be grounded

C. Die thickness = 381 µm

Table 1. Bare Die Information

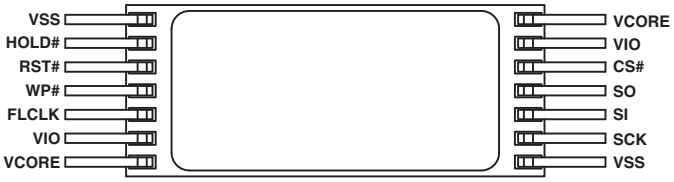
DIE THICKNESS	DIE PAD COMPOSITION	BACKSIDE FINISH	BACKSIDE POTENTIAL
15 Mils	AlCu/TiN	Silicon with backgrind	Float

Table 2. Bond Pad Coordinates

PAD NO.	DESCRIPTION	BOND PAD COORDINATES (μm)			
		X MIN	Y MIN	X MAX	Y MAX
1	VCORE	439.985	11182.64	525.035	11267.69
73	VSS	449.715	82.11	534.765	167.16
74	HOLD#	989.765	82.11	1074.815	167.16
75	RST#	1529.815	82.11	1614.865	167.16
76	WP#	2069.865	82.11	2154.915	167.16
77	FLCLK	2609.915	82.11	2694.965	167.16
78	VIO	3149.965	82.11	3235.015	167.16
79	VCORE	3690.015	82.11	3775.065	167.16
145	VSS	3680.285	11182.64	3765.335	11267.69
146	SCK	3144.155	11182.64	3229.205	11267.69
147	SI	2600.185	11182.64	2685.235	11267.69
148	SO	2049.985	11182.64	2135.035	11267.69
149	CS#	1520.085	11182.64	1605.135	11267.69
150	VIO	980.035	11182.64	1065.085	11267.69

DEVICE INFORMATION

HKN PACKAGE PIN ASSIGNMENT (TOP VIEW)



TERMINAL FUNCTIONS

TERMINAL		TYPE	DESCRIPTION
NAME	NO.		
VIO	6, 13	Power	3.3-V supply for IO
VCORE	7, 14	Power	1.9-V supply for core
VSS	1, 8	Ground	Device ground
CS#	12	Input	Active low SPI chip select
SCK	9	Input	SPI clock for serial communication
SI	10	Input	SPI data input to device
SO	11	Output	SPI data output from device (Hi impedance when CS# is 1)
HOLD#	2	Input	Active low hold input to freeze SPI communication
WP#	4	Input	Active low input for sector protection
RST#	3	Input	Active low reset to IC
FLCLK	5	Input	Flash pump clock

FUNCTIONAL BLOCK DIAGRAM

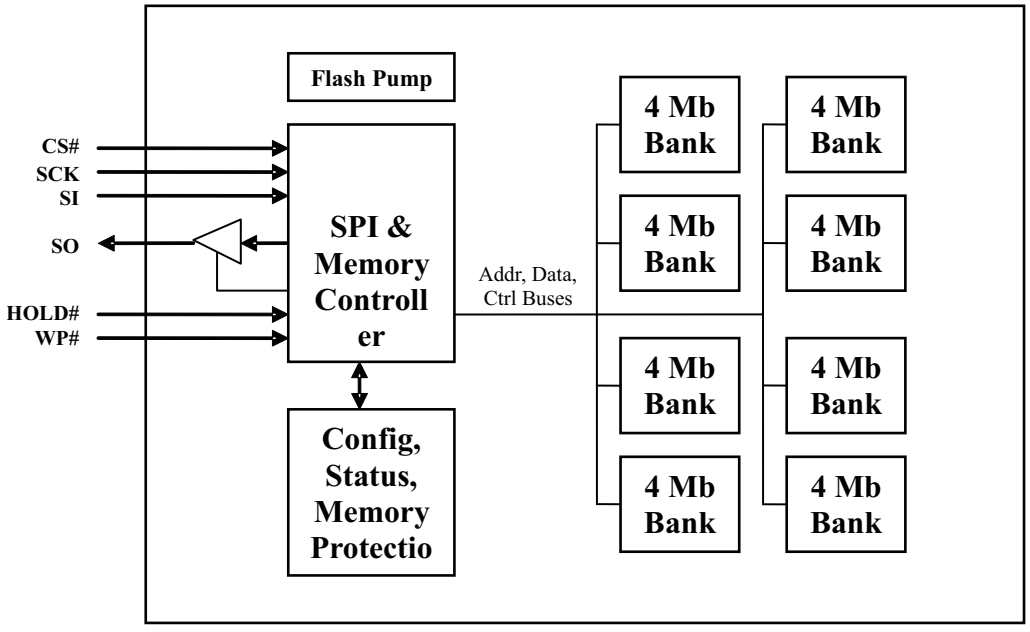


Figure 4. Block Diagram of SM28VLT32 and Memory Architecture

DETAILED DESCRIPTION

SERIAL COMMUNICATION

SM28VLT32 supports mode 0 and mode 3 SPI protocols. In mode 0, the inactive state of SCK is 0 whereas, in mode 3, the state is 1. The input data on SI is always latched on rising edge of SCK and data on SO is output on falling edge of SCK in both modes. CS# is brought low to start a new SPI data frame. The SPI data frame consists of an 8-bit command byte followed by a variable number of bytes of input data as shown in Table 3. The first 8 bits of SO always output the quick status bits. These bits define error conditions and status of the FLASH (see Table 4). These bits should be evaluated after each command is executed to determine if the preceding command completed successfully. This can be implemented as part of the SPI communication protocol with the host device. For more information see the Application Information section. The output data on SO follows after the complete data is provided to the device on SI pin. Invalid command bytes are ignored. Also, any additional SCK clock cycles and additional data on SI beyond the depicted frame size are ignored. CS# going high delineates the end of current data frame.

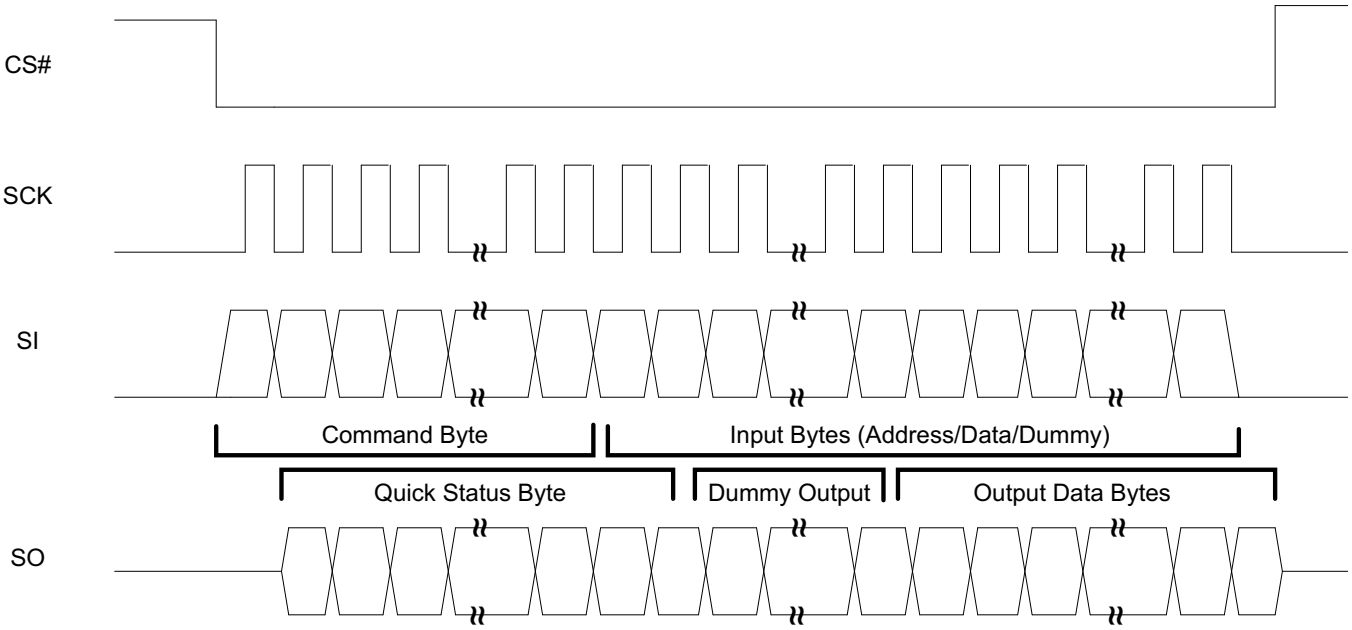


Figure 5. SPI Data Frame to Read, Write, Erase Memory Data and to Access Config/Status Registers

Table 3. Serial Peripheral Interface (SPI) Data Frame(1)

COMMAND NAME	COMMAND BYTE ON SI	ADDRESS BYTES ON SI	DATA BYTES ON SI	DUMMY BYTES ON SI(2)	DATA BYTES ON SO	TOTAL BYTES IN FRAME	DESCRIPTION
Read Word	15h	3	0	1 (3)	2	7	Read word at given address
Read Word with auto addressing	16h	0	0	1 (3)	2	4	Burst read from previous address
Write Word	17h	3	2	1 (1)	0	7	Write word at given address
Write Word with auto addressing	18h	0	2	1 (1)	0	4	Burst write from previous address
Erase Segment(3)	19h	3	0	1 (1)	0	5	Erase addressed segment
Read Status Register	22	0	0	0 (2)	2	3	Read SPI status register
Validate Segment	1A	3	0	1 (1)	0	5	Validates addressed segment
Write Register	1D	3	2	1 (1)	0	7	Writes to address in configuration register
Read Register	1E	3	0	1 (3)	2	7	Reads from address in configuration register
Write Command	1F	0	2	1 (1)	0	4	Flash controller command interface for special functions. See Application Information section.

(1) Multi-byte inputs and results are MSB first, LSB last.
(2) (#) indicates total number of dummy SI bytes including overlap with SO output.
(3) Permanent damage to flash array may occur if erase is executed when T_J exceeds 125°C.

REGISTER DEFINITIONS

Table 4. Quick Status Register

BITS	DEFAULT VALUE	TYPE	DESCRIPTION
7	0	R	Unused
6	0	R	SPI Frame error: indicates frame ended with less than required bytes to complete
5	0	R	Write Busy: indicates that a program operation is in progress
4	0	R	Erase Busy: indicates that a sector is being erased
3	0	R	Device Busy
2	0	R	Invalid Data: indicates that an attempt was made to set a bit to 1 that has already been programmed to 0
1	0	R	Read error: indicates that read was attempted on address when data was not available
0	0	R	Command error: indicates that a prior command failed. Must be cleared.

Table 5. Status Register (Command 22h)

BITS	DEFAULT VALUE	TYPE	DESCRIPTION
15:12	0	R	Reserved
11:08	RevID	R	Revision ID (current revision 1001)
7	0	R	Unused
6	0	R	Read Busy
5	0	R	Write Busy
4	0	R	Erase Busy
3	0	R	Write Suspend
2	0	R	Erase Suspend
1	0	R	Flash Pump Ready
0	0	R	SPI Frame error

APPLICATION INFORMATION

The quick status register is intended to be used as feedback of device and command status. The host should evaluate the quick status results at each command execution to determine device status. Additionally, two of the error fields in the quick status are sticky. They will need to be intentionally cleared by the host once detected. The Command and Invalid Data error flags will not self clear. The command error bit indicates that a command failed. This can be either an erase or program command. If this was a program attempt, then the data written may not be valid. The host may decide to re-write this data or pursue some other error recovery path. The Invalid data bit will get set if an attempt to write a bit to a logical 1 (erased state) in a word that has that bit already programmed to a 0. This would likely be the first error seen when writing to an array that contains data. To clear a Command error or Invalid Data error, the host must execute the following SPI command sequence: 1F 00 40 xx. xx is a dummy byte and values are don't care. This SPI command is a special command that is sent to the internal flash controller to clear errors.

It is important to note that the quick status capture of the internal setting of the Command error and the Invalid Data flags are delayed by one transaction. Similarly, the Device Busy flag does not get cleared until a second transaction. For example, in the case of polling after a write. If this write generated an Invalid Data error, the sequence would be as follows.

SPI WRITE	SPI READ	DESCRIPTION
0x17_0000_FFFF	00_xxxx_xxxx	Write to address 0 with erased value This will cause Invalid Data error if word has been programmed.
0xFF	08	Execute quick status. This result is Device Busy.
0xFF	04	Execute quick status with Invalid Data error.

Similarly, if a write or program fails, then the Command error status will show on the second transaction after the failed command. To effectively deal with this in a protocol, the best method is to poll the quick status twice to validate no error occurred. For applications that this method is too costly for SPI bandwidth, the error can be trapped on execution of the following commands with the knowledge that the error belonged to the command 2 transactions earlier.

The SPI Frame error and the Read error are errors that return correct status on the next quick status. These two errors are not sticky and only apply to the prior transaction.

Provisions for Operating With f_{CLK} Frequencies Less than 12 MHz

The SM28VLT32 uses a state machine and registers to implement the correct algorithms for programing, erasure and validation. The register values define counters and loops that determine appropriate setup and hold times, maximum attempts, pulse widths, and other critical parameters. The default values of these registers are defined for f_{CLK} operation in the 10 MHz to 12 MHz range. Operating below 10 MHhz requires changing key registers to properly implement the algorithm. See Table 6 for register settings for specific f_{CLK} ranges. Note, the 10 MHz to 12 MHz values are provided, but are not required to be written as they are the reset defaults. Additionally, the SPI S_{CLK} frequency must be 5/6ths of f_{CLK} or slower for reliable operation.

The values below represent the address and value that should be written using the 1D command. Note that first line is a write to F004. This must be first, as it unlocks the test control register and allows modification of the memory mapped registers. Without this write, the contents of the register would not change. It is recommended to follow the register writes with a read to verify that change was properly implemented. The last line is a write back to the test control register to relock it preventing accidental modification of the registers.

Table 6. Required Register Modifications for Operating at Frequencies Below 10 MHz(1)

ADDRESS	12-10 MHz	10-8 MHz	8-6 MHz	6-4 MHz	4-2 MHz	
F004	2BC0	2BC0	2BC0	2BC0	2BC0	Unlock TCR
8006	0764	0654	0544	0434	0324	
8008	307D	3064	3050	303C	3028	
8009	0D0D	0A0A	0808	0606	0404	
8010	0D0D	0A0A	0808	0606	0404	
8014	0032	0028	0020	0018	0010	
8015	83D6	6978	5460	3F48	2A30	
8016	186A	1388	0FA0	0BB8	07D0	
8017	0D0D	0A0A	0808	0606	0404	
8018	0064	0050	0040	0030	0020	
800D	0D0D	0A0A	0808	0606	0404	
800E	01F4	0190	0140	00F0	00A0	
F004	03C0	03C0	03C0	03C0	03C0	Lock TCR

(1) f_{CLK} cannot be operated lower than 2 MHz.

Initialization of the register values must be repeated on power cycle or RST assertion.

Power Supply Sequencing

The ideal power supply sequence is VCORE coming up before VIO (VCORE > 1.65 V before V_{IO} greater than 0.8 V).

For powerdown, the reverse is also true. VIO should be below 0.8 V before VCORE is < 1.65 V.

Alternatively, VIO can come up first or simultaneously with VCORE if RST is asserted low until both supplies are within recommended operating range. Similarly if device is active, it is necessary to assert RST prior to powering down to minimize chance of corrupting the flash array.

Power Saving Features

The device has power saving capabilities that allow it to be put into either standby or sleep states for the banks and flash pump when periods of inactivity are detected. When an access is initiated during sleep or standby, the pump and banks will transition to the active state automatically. Use of these features does not have protocol impact on programming (other than additional time required to wake up), as the device will report Write Busy. However, during read operations, the device will report Read error on next quick status read. This is due to the fact that a read transaction is immediate, while a write is queued. The value read from an address that is in standby or sleep will be 00 00. Reference Application Note: "Using the SM28VLT32-HT With Power Saving Features" (SLVA550).

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SM28VLT32SHKN	ACTIVE	CFP	HKN	14	10	TBD	AU	N / A for Pkg Type	-55 to 210	28VLT32S HKN	Samples
SM28VLT32SKGD3	ACTIVE	XCEPT	KGD	0	12	TBD	Call TI	N / A for Pkg Type	-55 to 210		Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

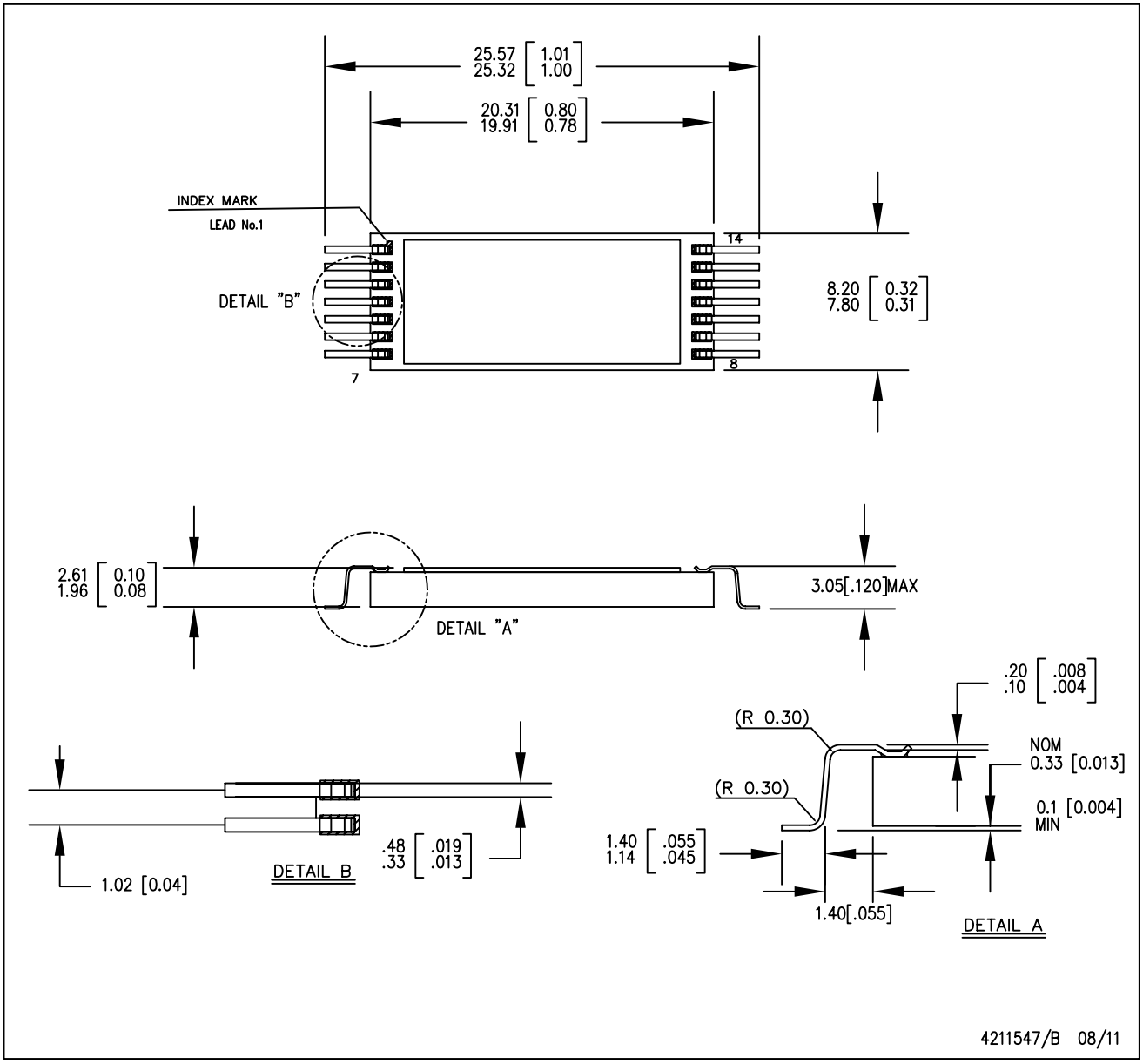
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

HKN (S–CDFP–G14) CERAMIC GULL WING



NOTES:
A. All linear dimensions are in millimeters [inches].
B. This drawing is subject to change without notice.
C. Ceramic with gull formed leads.
D. This package is hermetically sealed with a metal lid.
E. The leads are gold plated and can be solderdipped.
F. Lid is not connected to any lead.

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